
2SC5593

Silicon NPN Epitaxial High Frequency Low Noise Amplifier

HITACHI

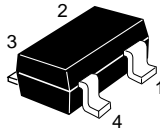
ADE-208-797 (Z)
1st. Edition
Nov. 2000

Features

- High gain bandwidth product
 $f_T = 23$ GHz typ.
- High power gain and low noise figure ;
PG = 18 dB typ. , NF = 1.8 dB typ. at $f = 1.8$ GHz

Outline

CMPAK-4



1. Emitter
2. Collector
3. Emitter
4. Base

Note: Marking is "XH".

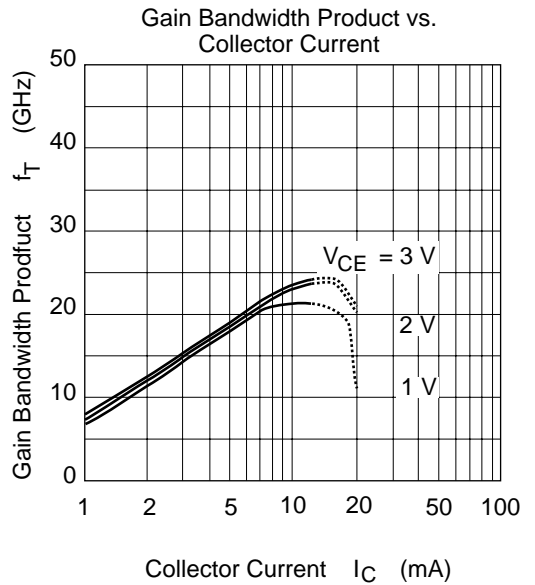
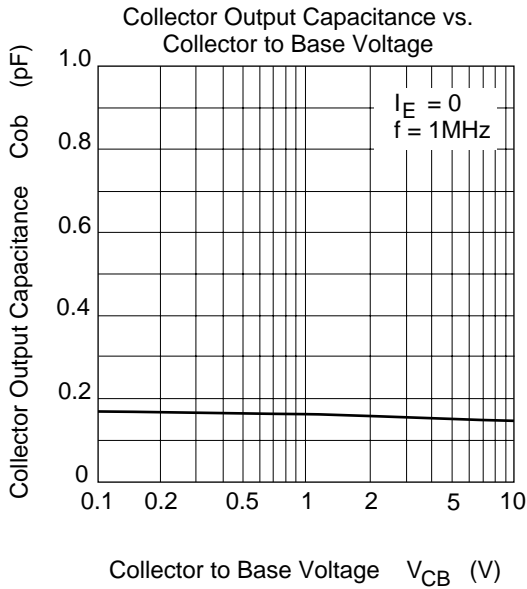
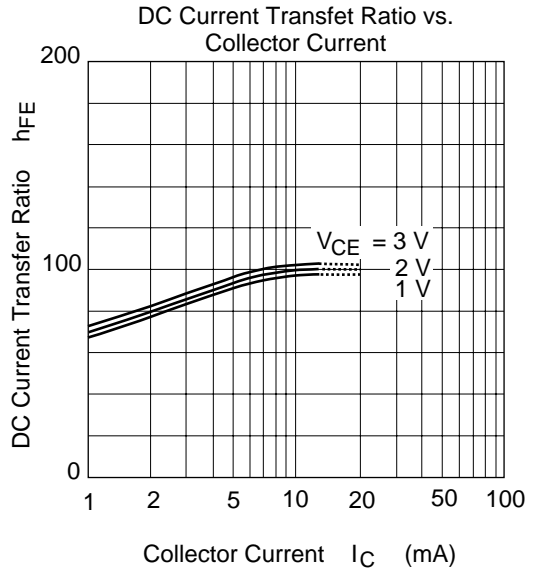
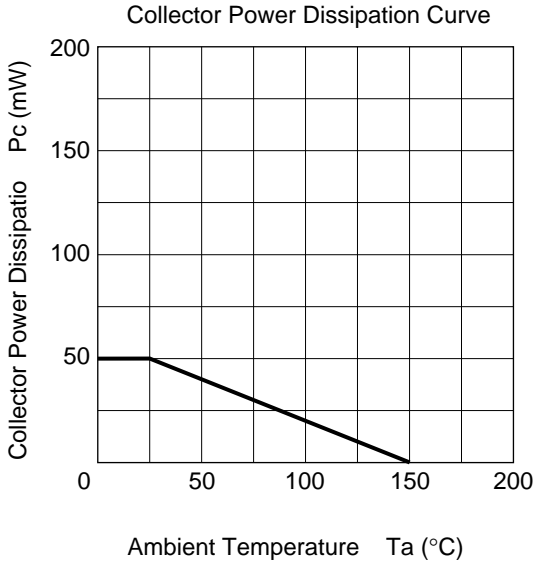
Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

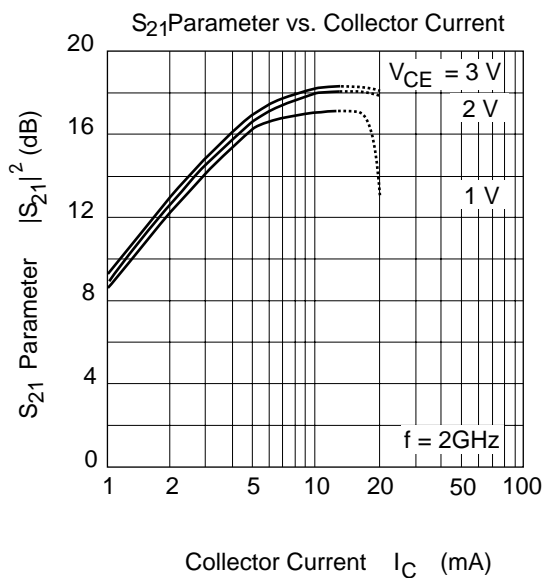
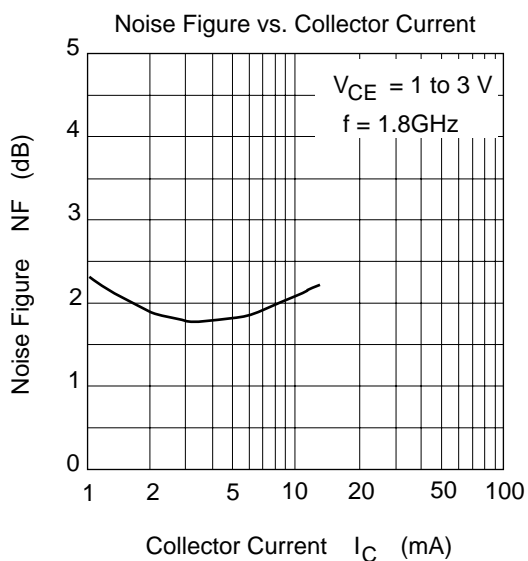
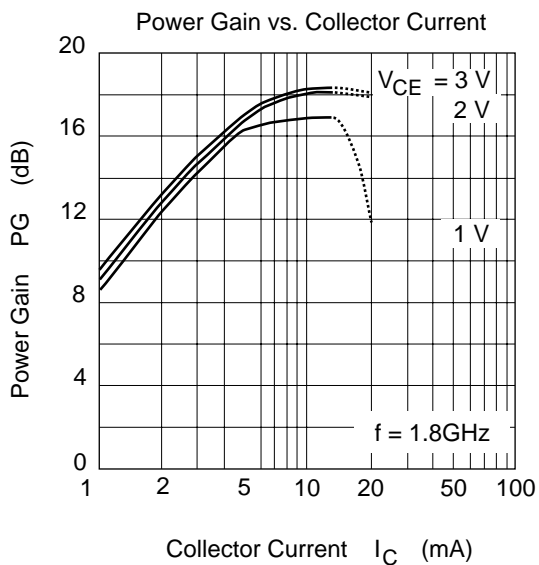
Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	12	V
Collector to emitter voltage	V_{CEO}	4.5	V
Emitter to base voltage	V_{EBO}	1	V
Collector current	I_{C}	12	mA
Collector power dissipation	P_{C}	50	mW
Junction temperature	T_{j}	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

Electrical Characteristics ($T_a = 25^\circ\text{C}$)

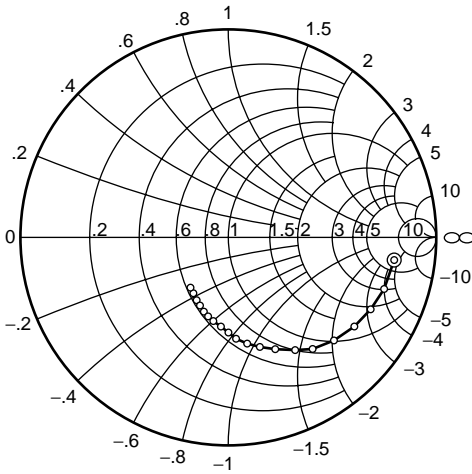
Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Collector to base breakdown voltage	$V_{(\text{BR})\text{CBO}}$	12	—	—	V	$I_{\text{C}} = 10 \mu\text{A}$, $I_{\text{E}} = 0$
Collector cutoff current	I_{CBO}	—	—	1	μA	$V_{\text{CB}} = 10 \text{ V}$, $I_{\text{E}} = 0$
Collector cutoff current	I_{CEO}	—	—	1	μA	$V_{\text{CE}} = 4 \text{ V}$, $R_{\text{BE}} = \infty$
Emitter cutoff current	I_{EBO}	—	—	12	μA	$V_{\text{EB}} = 1 \text{ V}$, $I_{\text{C}} = 0$
DC current transfer ratio	h_{FE}	60	100	140	V	$V_{\text{CE}} = 2 \text{ V}$, $I_{\text{C}} = 10 \text{ mA}$
Collector output capacitance	C_{ob}	—	0.16	0.4	pF	$V_{\text{CB}} = 2 \text{ V}$, $I_{\text{E}} = 0$ $f = 1 \text{ MHz}$
Gain bandwidth product	f_{T}	20	23	—	GHz	$V_{\text{CE}} = 2 \text{ V}$, $I_{\text{C}} = 10 \text{ mA}$ $f = 2 \text{ GHz}$
Power gain	PG	14	18	—	dB	$V_{\text{CE}} = 2 \text{ V}$, $I_{\text{C}} = 10 \text{ mA}$ $f = 1.8 \text{ GHz}$
Noise figure	NF	—	1.8	2.3	dB	$V_{\text{CE}} = 2 \text{ V}$, $I_{\text{C}} = 3 \text{ mA}$ $f = 1.8 \text{ GHz}$

Main Characteristics





S11 Parameter vs. Frequency

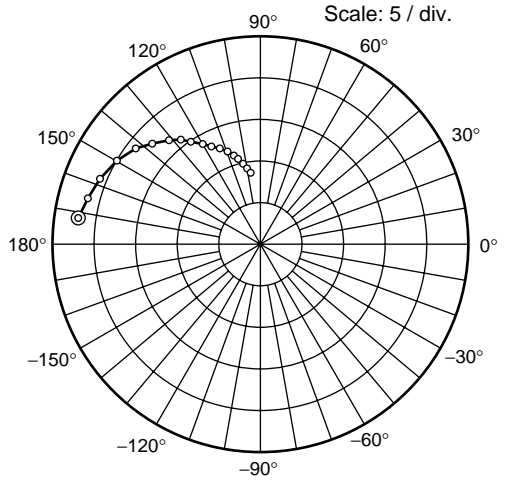


Condition : $V_{CE} = 2\text{ V}$, $I_C = 10\text{ mA}$

100 to 2000 MHz (100 MHz step)

⊙—○

S21 Parameter vs. Frequency

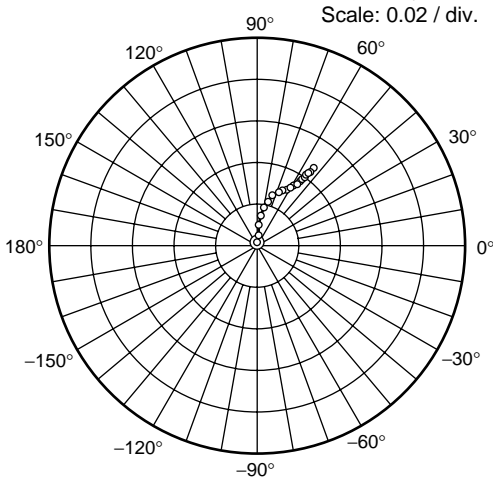


Condition : $V_{CE} = 2\text{ V}$, $I_C = 10\text{ mA}$

100 to 2000 MHz (100 MHz step)

⊙—○

S12 Parameter vs. Frequency

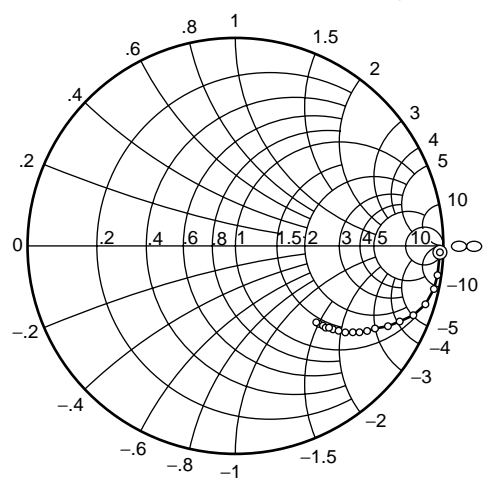


Condition : $V_{CE} = 2\text{ V}$, $I_C = 10\text{ mA}$

100 to 2000 MHz (100 MHz step)

⊙—○

S22 Parameter vs. Frequency



Condition : $V_{CE} = 2\text{ V}$, $I_C = 10\text{ mA}$

100 to 2000 MHz (100 MHz step)

⊙—○

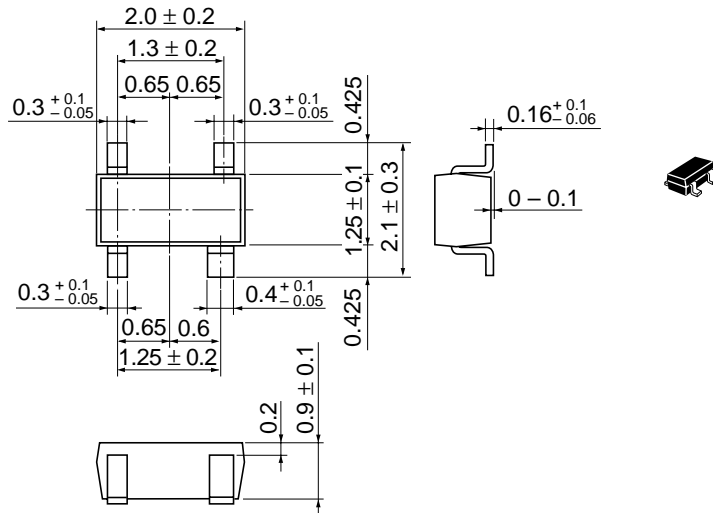
S-parameter ($V_{CE} = 2\text{ V}$, $I_C = 10\text{ mA}$, $Z_o = 50\ \Omega$)

f (MHz)	S11		S21		S12		S22	
	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
100	0.804	-8.2	22.02	172.5	0.00305	94.6	0.993	-3.4
200	0.795	-17.8	21.55	165.0	0.0067	86.8	0.986	-8.1
300	0.776	-27.4	20.88	157.5	0.0107	85.4	0.972	-12.7
400	0.746	-35.8	20.05	150.2	0.0146	82.5	0.947	-17.2
500	0.714	-44.5	18.93	143.7	0.0182	78.4	0.917	-21.2
600	0.673	-53.2	17.84	137.9	0.0215	74.8	0.881	-25.1
700	0.632	-59.9	16.60	132.5	0.0249	71.8	0.842	-28.3
800	0.595	-67.1	15.69	127.9	0.0274	67.9	0.808	-31.2
900	0.557	-74.6	14.64	123.5	0.0296	65.1	0.763	-33.7
1000	0.519	-79.1	13.68	119.5	0.0319	63.6	0.729	-35.6
1100	0.488	-86.0	12.88	116.0	0.0337	61.6	0.696	-37.2
1200	0.454	-91.1	12.03	112.8	0.0350	60.4	0.666	-38.6
1300	0.430	-95.9	11.26	110.6	0.0366	58.8	0.644	-39.5
1400	0.403	-101.8	10.69	107.8	0.0382	57.4	0.619	-40.6
1500	0.377	-106.3	10.16	105.4	0.0401	56.6	0.598	-41.2
1600	0.364	-111.0	9.66	103.6	0.0410	56.3	0.581	-42.0
1700	0.346	-116.6	9.19	101.4	0.0422	55.6	0.564	-42.6
1800	0.327	-120.0	8.79	99.3	0.0435	55.2	0.550	-43.2
1900	0.313	-124.9	8.40	97.5	0.0447	55.2	0.537	-43.9
2000	0.296	-130.8	7.99	95.5	0.0457	54.8	0.525	-44.0

Package Dimensions

As of January, 2001

Unit: mm



Hitachi Code	CMPAK-4(T)
JEDEC	—
EIAJ	Conforms
Mass (reference value)	0.006 g

Cautions

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HITACHI

Hitachi, Ltd.

Semiconductor & Integrated Circuits.
 Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan
 Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109

URL	NorthAmerica	: http://semiconductor.hitachi.com/
	Europe	: http://www.hitachi-eu.com/hel/ecg
	Asia	: http://sicapac.hitachi-asia.com
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For further information write to:

Hitachi Semiconductor
 (America) Inc.
 179 East Tasman Drive,
 San Jose, CA 95134
 Tel: <1> (408) 433-1990
 Fax: <1> (408) 433-0223

Hitachi Europe GmbH
 Electronic Components Group
 Dornacher Straße 3
 D-85622 Feldkirchen, Munich
 Germany
 Tel: <49> (89) 9 9180-0
 Fax: <49> (89) 9 29 30 00

Hitachi Europe Ltd.
 Electronic Components Group.
 Whitebrook Park
 Lower Cookham Road
 Maidenhead
 Berkshire SL6 8YA, United Kingdom
 Tel: <44> (1628) 585000
 Fax: <44> (1628) 585160

Hitachi Asia Ltd.
 Hitachi Tower
 16 Collyer Quay #20-00,
 Singapore 049318
 Tel : <65>-538-6533/538-8577
 Fax : <65>-538-6933/538-3877
 URL : <http://www.hitachi.com.sg>

Hitachi Asia Ltd.
 (Taipei Branch Office)
 4/F, No. 167, Tun Hwa North Road,
 Hung-Kuo Building,
 Taipei (105), Taiwan
 Tel : <886>-(2)-2718-3666
 Fax : <886>-(2)-2718-8180
 Telex : 23222 HAS-TP
 URL : <http://www.hitachi.com.tw>

Hitachi Asia (Hong Kong) Ltd.
 Group III (Electronic Components)
 7/F., North Tower,
 World Finance Centre,
 Harbour City, Canton Road
 Tsim Sha Tsui, Kowloon,
 Hong Kong
 Tel : <852>-(2)-735-9218
 Fax : <852>-(2)-730-0281
 URL : <http://www.hitachi.com.hk>

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